

YJ Planar Schottky Barrier Diode Die Specification

150V 20A, 102mil, Schottky barrier diode die based on silicon planar process
Part No.: PSB102H150AS-280A

Main Products Characterstics

Maximum Ratings

Symbol	Parameter	Value
I_F	Forward Current	20 A
V_F	Forward Voltage	1.0 V
I_{RMS}	RMS Reverse Current	100 μ A
V_R	Reverse Voltage	150 V
T_J	Junction Temperature	175 °C
T_{stg}	Storage Temperature	-55 ~ 175 °C

Device Schematics and Outline Drawing

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Important Notice

Specification apply to die only. Actual performance may degrade when assembled.
We do not guarantee device performance after assembly.

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Static Electrical Characteristics (Ta = 25°C)

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Die Thickness *
Die Size **
Top Metal Pad
Active Area

Top Metal
Back Metal
Note: 1 * : Also can offer device with 8 mils thickness
2 **: Cutting street width is around 1.5 mils

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